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Simulation, Modeling, and Crystal Growth of $\text{Cd}_{0.9}\text{Zn}_{0.1}\text{Te}$ for Nuclear Spectrometers

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In the above mentioned article, two references were regrettably omitted from the final paragraph in the first column of page 1253, and inappropriately similar wording to the original references was used. The authors sincerely apologize to the authors of the references and the journal readership for this error.

Please replace the passage “Notably, the CZT crystal... ..growth of other semiconductors.” with “CZT melt exists as a semiconductor¹ with the Prandtl number of $\text{Pr} = 0.41$, which is a few orders of magnitude larger than that of most semiconductor materials, such as Si, GaAs, and InP. The $\text{Pr} = 0.41$ causes a strong coupling between thermal and momentum transport, which leads to instabilities in the growth of CZT crystal.”²

REFERENCES

1. V.V. Godlevsky, J.J. Derby, and J.R. Chelikowsky, *Phys. Rev. Lett.* 81, 4959 (1998).
2. A. Yeckel, F.P. Doty, and J.J. Derby, *J. Cryst. Growth* 203, 87 (1999).